

MA2J115

Silicon epitaxial planar type

For small power current rectification

■ Features

- Small S-mini type package, allowing high-density mounting
- High reverse voltage V_R

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

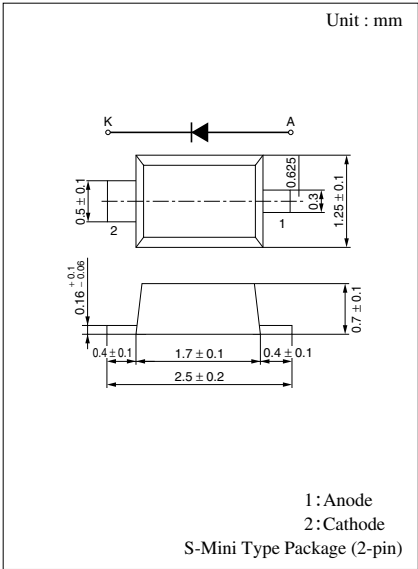
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	200	V
Peak reverse voltage	V_{RM}	200	V
Output current	I_O	200	mA
Repetitive peak forward current	I_{FRM}	600	mA
Non-repetitive peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) * : $t = 1 \text{ s}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 200 \text{ V}$			200	nA
Forward voltage (DC)	V_F	$I_F = 200 \text{ mA}$			1.2	V
Terminal capacitance	C_t	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		4.5		pF

Note) Rated input/output frequency: 3 MHz



Marking Symbol: 1F

